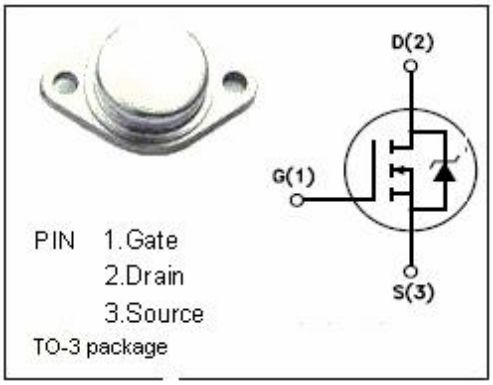
isc N-Channel Mosfet Transistor IRFAC32

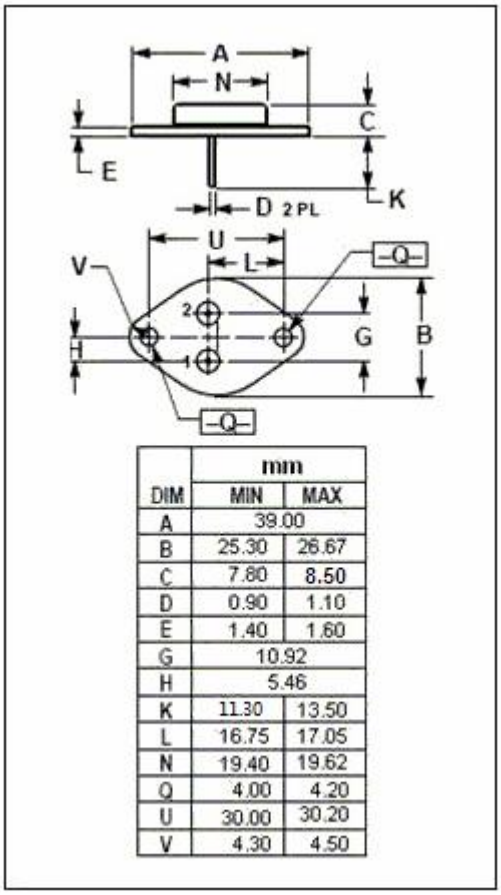
- **FEATURES**
- Lower Input Capacitance
- Improved Gate Charge
- Extended Safe Operating Area
- Rugged Gate Oxide Technology
- High speed switching
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



- **DESCRITION**
- High current ,high speed switching
- Switch mode power supplies
- DC-AC converters for welding equipment and Uninterruptible power supplies and motor Driver.

- **ABSOLUTE MAXIMUM RATINGS(T_a=25℃)**

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	600	V
V_{GS}	Gate-Source Voltage-Continuous	±20	V
I_D	Drain Current-Continuous	3.2	A
I_{DM}	Drain Current-Single Pluse	12.8	A
P_D	Total Dissipation @T_C=25℃	74	W
T_J	Max. Operating Junction Temperature	-55~150	℃
T_{stg}	Storage Temperature	-55~150	℃



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	1.67	℃/W
$R_{th\ j\text{-}a}$	Thermal Resistance, Junction to Ambient	30	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}= 0; I_D= 1mA	600		V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}; I_D= 0.25mA	2	4	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= 10V; I_D=2.3A		2.7	Ω
I_{GSS}	Gate-Body Leakage Current	V_{GS}= ±20V;V_{DS}= 0		±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= 480V; V_{GS}= 0		25	μA
V_{SD}	Forward On-Voltage	I_S= 3.2A; V_{GS}= 0		1.6	V